74LVC1G3157

2-channel analog multiplexer/demultiplexer

Rev. 02 — 18 September 2007 Product data sheet

1. General description

The 74LVC1G3157 is a low-power, low-voltage, high-speed Si-gate CMOS device.

The 74LVC1G3157 provides one analog multiplexer/demultiplexer with one digital select input (S), two independent inputs/outputs (Y0, Y1) and a common input/output (Z).

Schmitt trigger action at the select input makes the circuit tolerant of slower input rise and fall times across the entire V_{CC} range from 1.65 V to 5.5 V.

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- Very low ON resistance:
  - 7.5 Ω (typical) at V_{CC} = 2.7 V
  - 6.5 Ω (typical) at V_{CC} = 3.3 V
  - 6 Ω (typical) at V_{CC} = 5 V
- Switch current capability of 32 mA
- Break-before-make switching
- High noise immunity
- CMOS low power consumption
- TTL interface compatibility at 3.3 V
- Latch-up performance meets requirements of JESD 78 Class I
- ESD protection:
  - HBM JESD22-A114E exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Control input accepts voltages up to 5.5 V
- Multiple package options
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C

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3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC1G3157GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74LVC1G3157GV	–40 °C to +125 °C	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457
74LVC1G3157GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74LVC1G3157GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891

4. Marking

Table 2. Marking

Type number	Marking code
74LVC1G3157GW	YJ
74LVC1G3157GV	YJ
74LVC1G3157GM	YJ
74LVC1G3157GF	YJ

5. Functional diagram

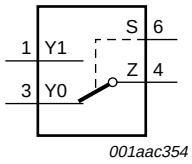


Fig 1. Logic symbol

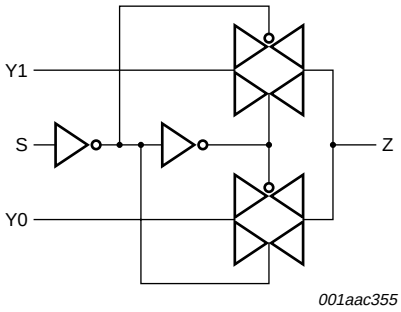


Fig 2. Logic diagram

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6. Pinning information

6.1 Pinning

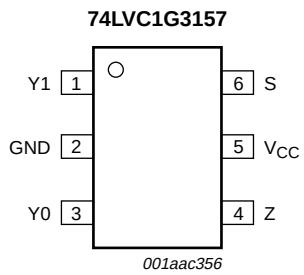


Fig 3. Pin configuration SOT363 and SOT457

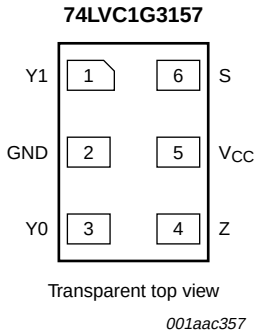


Fig 4. Pin configuration SOT886

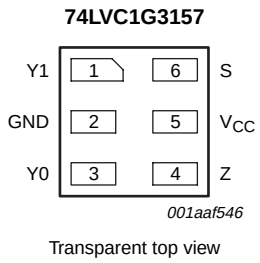


Fig 5. Pin configuration SOT891

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
Y1	1	independent input or output
GND	2	ground (0 V)
Y0	3	independent input or output
Z	4	common output or input
V_{CC}	5	supply voltage
S	6	select input

7. Functional description

Table 4. Function table[1]

Input S	Channel on
L	Y0
H	Y1

[1] H = HIGH voltage level;
L = LOW voltage level.

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+6.5	V
V_I	input voltage		[1]	–0.5	+6.5	V
I_{IK}	input clamping current	$V_I < –0.5$ V or $V_I > V_{CC} + 0.5$ V		–50	-	mA
I_{SK}	switch clamping current	$V_I < –0.5$ V or $V_I > V_{CC} + 0.5$ V		-	±50	mA
V_{SW}	switch voltage	enable and disable mode	[2]	–0.5	$V_{CC} + 0.5$	V
I_{SW}	switch current	$V_{SW} > –0.5$ V or $V_{SW} < V_{CC} + 0.5$ V		-	±50	mA
I_{CC}	supply current			-	100	mA
I_{GND}	ground current			–100	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = –40$ °C to +125 °C	[3]	-	250	mW

[1] The minimum input voltage rating may be exceeded if the input current rating is observed.

[2] The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed.

[3] For SC-88 and SC-74 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.
For XSON6 packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{CC}	supply voltage			1.65	-	5.5	V
V_I	input voltage			0	-	5.5	V
V_{SW}	switch voltage	enable and disable mode	[1]	0	-	V_{CC}	V
T_{amb}	ambient temperature			–40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.65$ V to 2.7 V	[2]	-	-	20	ns/V
		$V_{CC} = 2.7$ V to 5.5 V	[2]	-	-	10	ns/V

[1] To avoid sinking GND current from terminal Z when switch current flows in terminal Yn, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal Z, no GND current will flow from terminal Yn. In this case, there is no limit for the voltage drop across the switch.

[2] Applies to control signal levels.

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

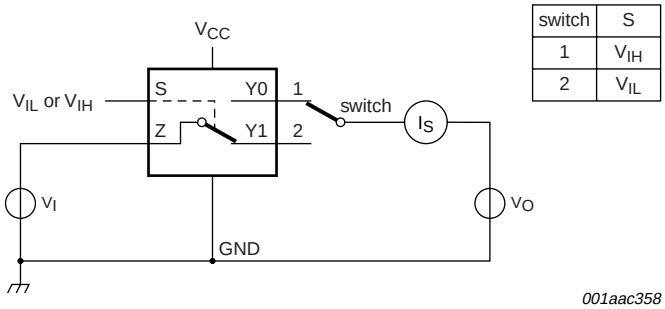
Symbol	Parameter	Conditions		–40 °C to +85 °C			–40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	
V_{IH}	HIGH-level input voltage	V_{CC} = 1.65 V to 1.95 V		0.65V_{CC}	-	-	0.65V_{CC}	-	V
		V_{CC} = 2.3 V to 2.7 V		1.7	-	-	1.7	-	V
		V_{CC} = 3 V to 3.6 V		2.0	-	-	2.0	-	V
		V_{CC} = 4.5 V to 5.5 V		0.7V_{CC}	-	-	0.7V_{CC}	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 1.65 V to 1.95 V		-	-	0.35V_{CC}	-	0.35V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V		-	-	0.7	-	0.7	V
		V_{CC} = 3 V to 3.6 V		-	-	0.8	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V		-	-	0.3V_{CC}		0.3V_{CC}	V
I_I	input leakage current	pin S; V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	[2]	-	±0.1	±2	-	±10	µA
$I_{S(OFF)}$	OFF-state leakage current	V_I = V_{IH} or V_{IL}; V_{CC} = 5.5 V; see Figure 6	[2]	-	±0.1	±5	-	±20	µA
$I_{S(ON)}$	ON-state leakage current	V_I = V_{IH} or V_{IL}; V_{CC} = 5.5 V; see Figure 7	[2]	-	±0.1	±5	-	±20	µA
I_{CC}	supply current	V_I = 5.5 V or GND; V_{SW} = GND or V_{CC}; I_O = 0 A; V_{CC} = 1.65 V to 5.5 V	[2]	-	0.1	10	-	40	µA
ΔI_{CC}	additional supply current	pin S; V_I = V_{CC} – 0.6 V; I_O = 0 A; V_{CC} = 5.5 V; V_{SW} = GND or V_{CC}	[2]	-	5	500	-	5000	µA
C_I	input capacitance			-	2.5	-	-	-	pF
$C_{S(OFF)}$	OFF-state capacitance			-	6.0	-	-	-	pF
$C_{S(ON)}$	ON-state capacitance			-	18	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C.

[2] These typical values are measured at V_{CC} = 3.3 V

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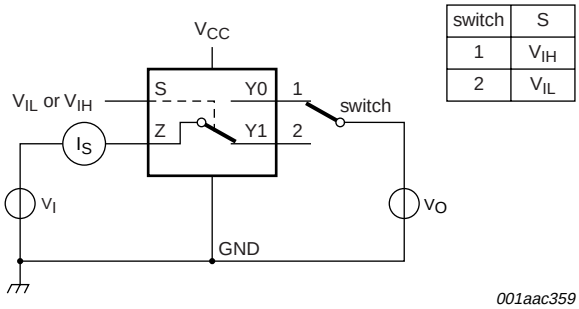
10.1 Test circuits



switch	S
1	V_{IH}
2	V_{IL}

$V_I = V_{CC}$ or GND and V_O = GND or V_{CC}.

Fig 6. Test circuit for measuring OFF-state leakage current



switch	S
1	V_{IH}
2	V_{IL}

$V_I = V_{CC}$ or GND and V_O = open circuit.

Fig 7. Test circuit for measuring ON-state leakage current

10.2 ON resistance

Table 8. ON resistance

At recommended operating conditions; voltages are referenced to GND (ground 0 V); for graphs see Figure 9 to Figure 14.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
$R_{ON(peak)}$	ON resistance (peak)	V_I = GND to V_{CC}; see Figure 8						
		I_{SW} = 4 mA; V_{CC} = 1.65 V to 1.95 V	-	34.0	130	-	195	Ω
		I_{SW} = 8 mA; V_{CC} = 2.3 V to 2.7 V	-	12.0	30	-	45	Ω
		I_{SW} = 12 mA; V_{CC} = 2.7 V	-	10.4	25	-	38	Ω
		I_{SW} = 24 mA; V_{CC} = 3 V to 3.6 V	-	7.8	20	-	30	Ω
		I_{SW} = 32 mA; V_{CC} = 4.5 V to 5.5 V	-	6.2	15	-	23	Ω

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Table 8. ON resistance *…continued*

At recommended operating conditions; voltages are referenced to GND (ground 0 V); for graphs see Figure 9 to Figure 14.

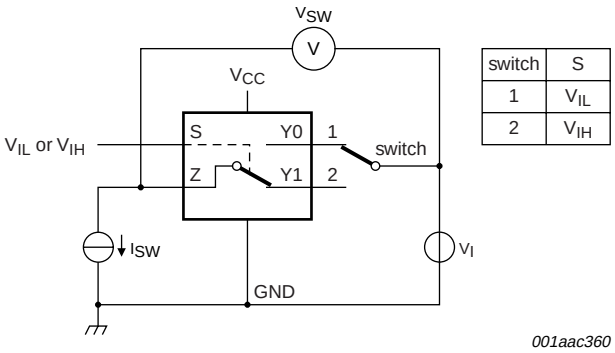
Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
$R_{ON(rail)}$	ON resistance (rail)	V_I = GND; see Figure 8						
		I_{SW} = 4 mA; V_{CC} = 1.65 V to 1.95 V	-	8.2	18	-	27	Ω
		I_{SW} = 8 mA; V_{CC} = 2.3 V to 2.7 V	-	7.1	16	-	24	Ω
		I_{SW} = 12 mA; V_{CC} = 2.7 V	-	6.9	14	-	21	Ω
		I_{SW} = 24 mA; V_{CC} = 3 V to 3.6 V	-	6.5	12	-	18	Ω
		I_{SW} = 32 mA; V_{CC} = 4.5 V to 5.5 V	-	5.8	10	-	15	Ω
		V_I = V_{CC}; see Figure 8						
		I_{SW} = 4 mA; V_{CC} = 1.65 V to 1.95 V	-	10.4	30	-	45	Ω
		I_{SW} = 8 mA; V_{CC} = 2.3 V to 2.7 V	-	7.6	20	-	30	Ω
		I_{SW} = 12 mA; V_{CC} = 2.7 V	-	7.0	18	-	27	Ω
		I_{SW} = 24 mA; V_{CC} = 3 V to 3.6 V	-	6.1	15	-	23	Ω
		I_{SW} = 32 mA; V_{CC} = 4.5 V to 5.5 V	-	4.9	10	-	15	Ω
$R_{ON(flat)}$	ON resistance (flatness)	V_I = GND to V_{CC} [2]						
		I_{SW} = 4 mA; V_{CC} = 1.65 V to 1.95 V	-	26.0	-	-	-	Ω
		I_{SW} = 8 mA; V_{CC} = 2.3 V to 2.7 V	-	5.0	-	-	-	Ω
		I_{SW} = 12 mA; V_{CC} = 2.7 V	-	3.5	-	-	-	Ω
		I_{SW} = 24 mA; V_{CC} = 3 V to 3.6 V	-	2.0	-	-	-	Ω
		I_{SW} = 32 mA; V_{CC} = 4.5 V to 5.5 V	-	1.5	-	-	-	Ω

[1] Typical values are measured at T_{amb} = 25 °C and nominal V_{CC}.

[2] Flatness is defined as the difference between the maximum and minimum value of ON resistance measured at identical V_{CC} and temperature.

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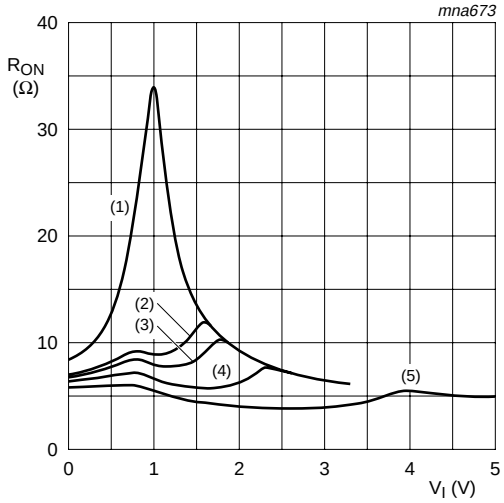
10.3 ON resistance test circuit and graphs



switch	S
1	V_{IL}
2	V_{IH}

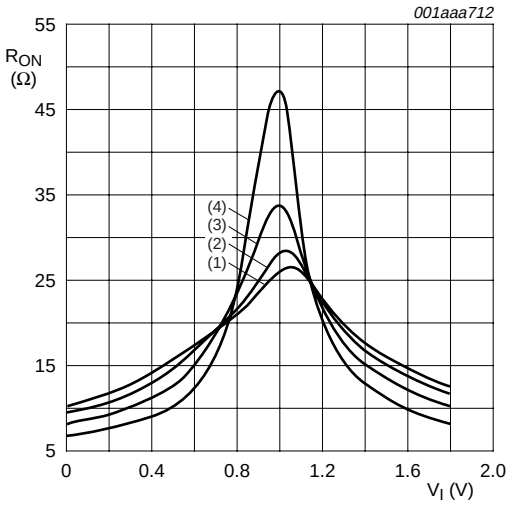
$R_{ON} = V_{SW} / I_{SW}$.

Fig 8. Test circuit for measuring ON resistance



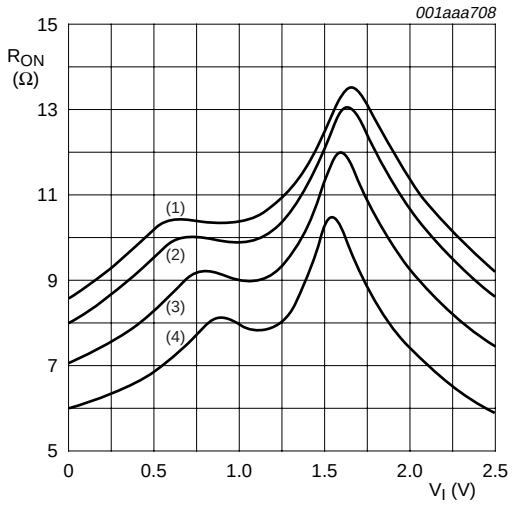
(1) V_{CC} = 1.8 V.
(2) V_{CC} = 2.5 V.
(3) V_{CC} = 2.7 V.
(4) V_{CC} = 3.3 V.
(5) V_{CC} = 5.0 V.

Fig 9. Typical ON resistance as a function of input voltage; T_{amb} = 25 °C



(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.
(4) T_{amb} = −40 °C.

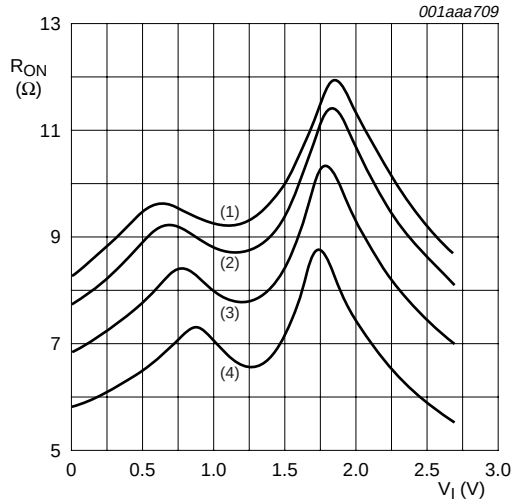
Fig 10. ON resistance as a function of input voltage; V_{CC} = 1.8 V



(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.
(4) T_{amb} = −40 °C.

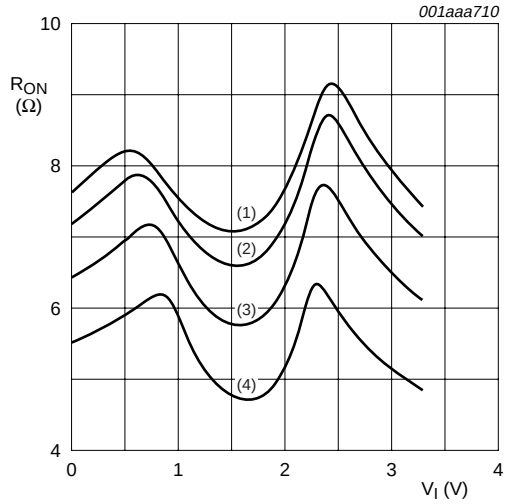
Fig 11. ON resistance as a function of input voltage; V_{CC} = 2.5 V

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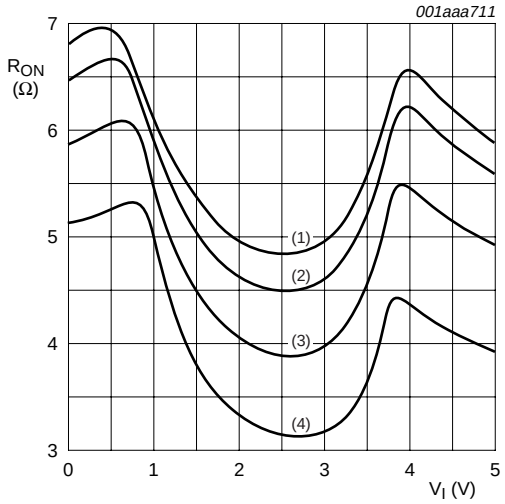
(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.
(4) T_{amb} = –40 °C.

Fig 12. ON resistance as a function of input voltage; V_{CC} = 2.7 V



(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.
(4) T_{amb} = –40 °C.

Fig 13. ON resistance as a function of input voltage; V_{CC} = 3.3 V



(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.
(4) T_{amb} = –40 °C.

Fig 14. ON resistance as a function of input voltage; V_{CC} = 5.0 V

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11. Dynamic characteristics

Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit see Figure 18.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	Z to Yn or Yn to Z; see Figure 15 [2][3]						
		V_{CC} = 1.65 V to 1.95 V	-	-	2	-	3.0	ns
		V_{CC} = 2.3 V to 2.7 V	-	-	1.2	-	2.0	ns
		V_{CC} = 2.7 V	-	-	1.0	-	1.5	ns
		V_{CC} = 3 V to 3.6 V	-	-	0.8	-	1.5	ns
		V_{CC} = 4.5 V to 5.5 V	-	-	0.6	-	1.0	ns
t_{en}	enable time	S to Yn; see Figure 16 [4]						
		V_{CC} = 1.65 V to 1.95 V	1.0	8.7	14	1.0	14.0	ns
		V_{CC} = 2.3 V to 2.7 V	1.0	5.3	7.5	1.0	7.5	ns
		V_{CC} = 2.7 V	1.0	4.9	6.0	1.0	6.0	ns
		V_{CC} = 3 V to 3.6 V	0.5	4.0	5.5	0.5	5.5	ns
		V_{CC} = 4.5 V to 5.5 V	0.5	3.0	4.0	0.5	4.0	ns
t_{dis}	disable time	S to Yn; see Figure 16 [5]						
		V_{CC} = 1.65 V to 1.95 V	2.5	6.0	8.5	2.5	8.5	ns
		V_{CC} = 2.3 V to 2.7 V	2.0	4.4	6.0	2.0	6.0	ns
		V_{CC} = 2.7 V	1.5	4.2	5.0	1.5	5.0	ns
		V_{CC} = 3 V to 3.6 V	1.5	3.6	4.5	1.5	4.5	ns
		V_{CC} = 4.5 V to 5.5 V	0.8	2.9	3.5	0.8	3.5	ns
t_{b-m}	break-before-make time	see Figure 17 [6]						
		V_{CC} = 1.65 V to 1.95 V	0.5	-	-	0.5	-	ns
		V_{CC} = 2.3 V to 2.7 V	0.5	-	-	0.5	-	ns
		V_{CC} = 2.7 V	0.5	-	-	0.5	-	ns
		V_{CC} = 3 V to 3.6 V	0.5	-	-	0.5	-	ns
		V_{CC} = 4.5 V to 5.5 V	0.5	-	-	0.5	-	ns

[1] Typical values are measured at T_{amb} = 25 °C and nominal V_{CC}.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] Propagation delay is the calculated RC time constant of the typical ON resistance of the switch and the specified capacitance when driven by an ideal voltage source (zero output impedance).

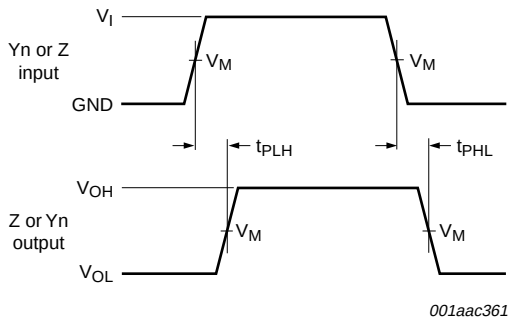
[4] t_{en} is the same as t_{PZH} and t_{PZL}.

[5] t_{dis} is the same as t_{PLZ} and t_{PHZ}.

[6] Break-before-make specified by design.

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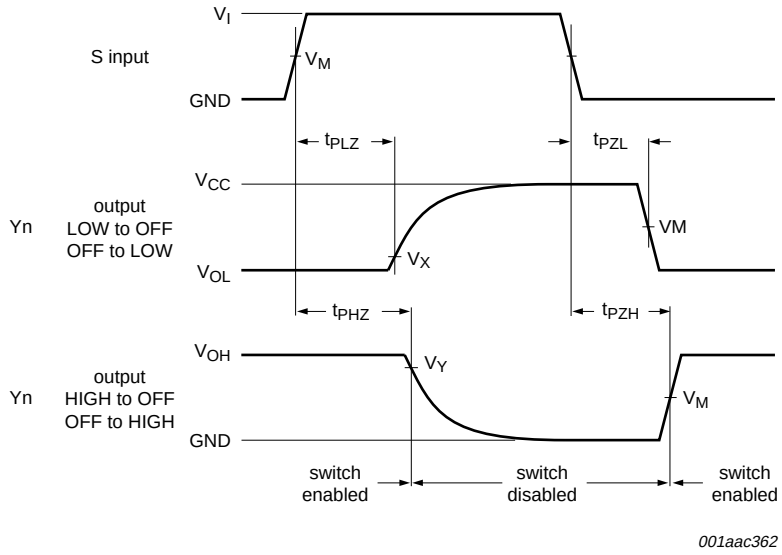
11.1 Waveforms and test circuits



Measurement points are given in Table 10.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 15. Input (Yn or Z) to output (Z or Yn) propagation delays



Measurement points are given in Table 10.

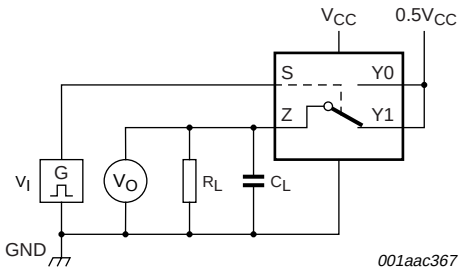
Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 16. Enable and disable times

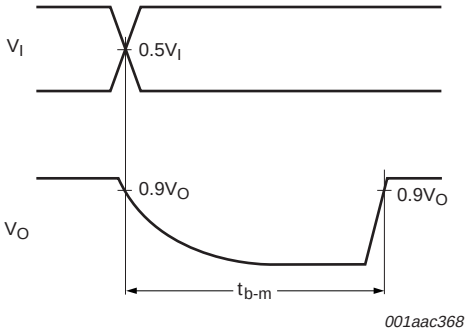
Table 10. Measurement points

Supply voltage	Input	Output		
V_{CC}	V_M	V_M	V_X	V_Y
1.65 V to 5.5 V	$0.5V_{CC}$	$0.5V_{CC}$	V_{OL} + 0.3 V	V_{OH} − 0.3 V

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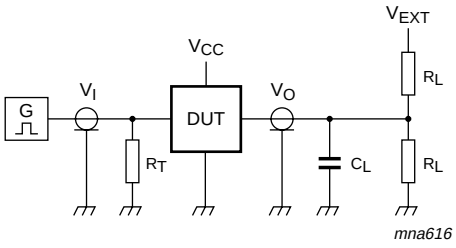


a. Test circuit



b. Input and output measurement points

Fig 17. Test circuit for measuring break-before-make timing



Test data is given in Table 11.

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

V_{EXT} = External voltage for measuring switching times.

Fig 18. Load circuit for switching times

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Table 11. Test data

Supply voltage	Input		Load		V_{EXT}		
V_{CC}	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	50 pF	500 Ω	open	GND	$2V_{CC}$
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	50 pF	500 Ω	open	GND	$2V_{CC}$
2.7 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	$2V_{CC}$
3 V to 3.6 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	$2V_{CC}$
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	$2V_{CC}$

11.2 Additional dynamic characteristics

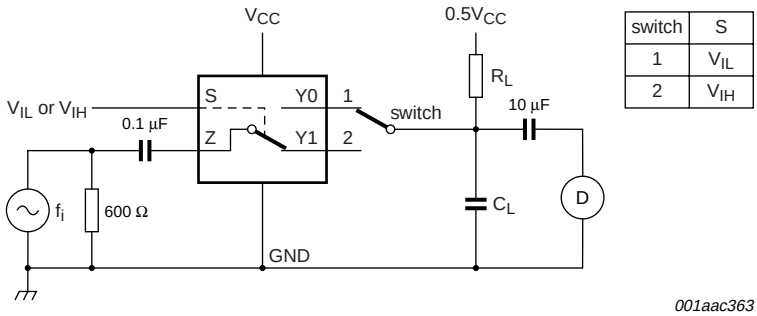
Table 12. Additional dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T_{amb} = 25 °C.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
THD	total harmonic distortion	f_i = 600 Hz to 20 kHz; R_L = 600 Ω; C_L = 50 pF; V_I = 0.5 V (p-p); see Figure 19				
		V_{CC} = 1.65 V	-	0.260	-	%
		V_{CC} = 2.3 V	-	0.078	-	%
		V_{CC} = 3.0 V	-	0.078	-	%
		V_{CC} = 4.5 V	-	0.078	-	%
$f_{(-3dB)}$	–3 dB frequency response	R_L = 50 Ω; C_L = 5 pF; see Figure 20				
		V_{CC} = 1.65 V	-	200	-	MHz
		V_{CC} = 2.3 V	-	300	-	MHz
		V_{CC} = 3.0 V	-	300	-	MHz
		V_{CC} = 4.5 V	-	300	-	MHz
α_{iso}	isolation (OFF-state)	R_L = 50 Ω; C_L = 5 pF; f_i = 10 MHz; see Figure 21				
		V_{CC} = 1.65 V	-	–42	-	dB
		V_{CC} = 2.3 V	-	–42	-	dB
		V_{CC} = 3.0 V	-	–40	-	dB
		V_{CC} = 4.5 V	-	–40	-	dB
Q_{inj}	charge injection	C_L = 0.1 nF; V_{gen} = 0 V; R_{gen} = 0 Ω; f_i = 1 MHz; R_L = 1 MΩ; see Figure 22				
		V_{CC} = 1.8 V	-	3.3	-	pC
		V_{CC} = 2.5 V	-	4.1	-	pC
		V_{CC} = 3.3 V	-	5.0	-	pC
		V_{CC} = 4.5 V	-	6.4	-	pC
		V_{CC} = 5.5 V	-	7.5	-	pC

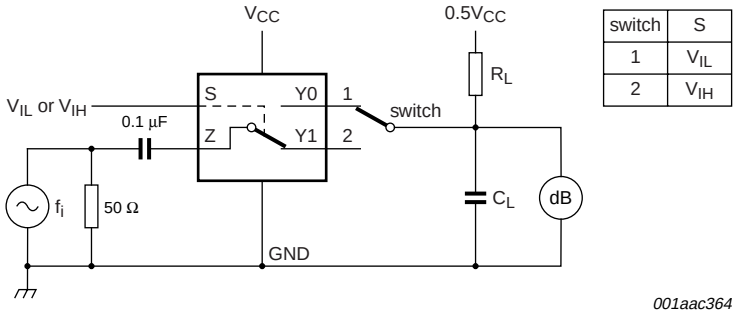
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11.3 Test circuits



switch	S
1	V_{IL}
2	V_{IH}

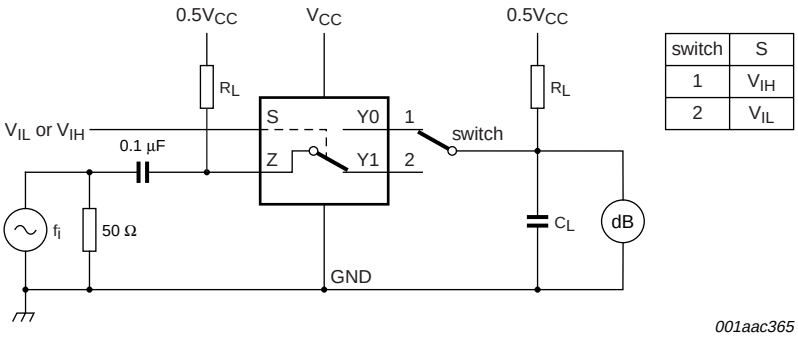
Fig 19. Test circuit for measuring total harmonic distortion



switch	S
1	V_{IL}
2	V_{IH}

Adjust f_i voltage to obtain 0 dBm level at output. Increase f_i frequency until dB meter reads −3 dB.

Fig 20. Test circuit for measuring the frequency response when switch is in ON-state

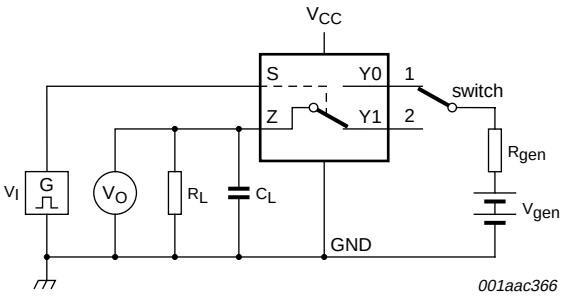


switch	S
1	V_{IH}
2	V_{IL}

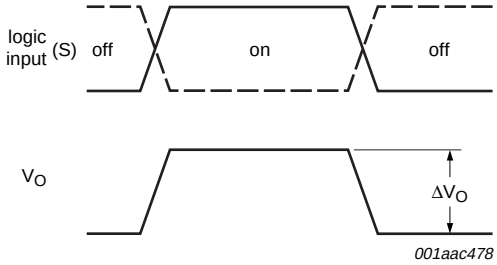
Adjust f_i voltage to obtain 0 dBm level at input.

Fig 21. Test circuit for measuring isolation (OFF-state)

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a. Test circuit



b. Input and output pulse definitions

$Q_{inj} = \Delta V_O \times C_L$.

ΔV_O = output voltage variation.

R_{gen} = generator resistance.

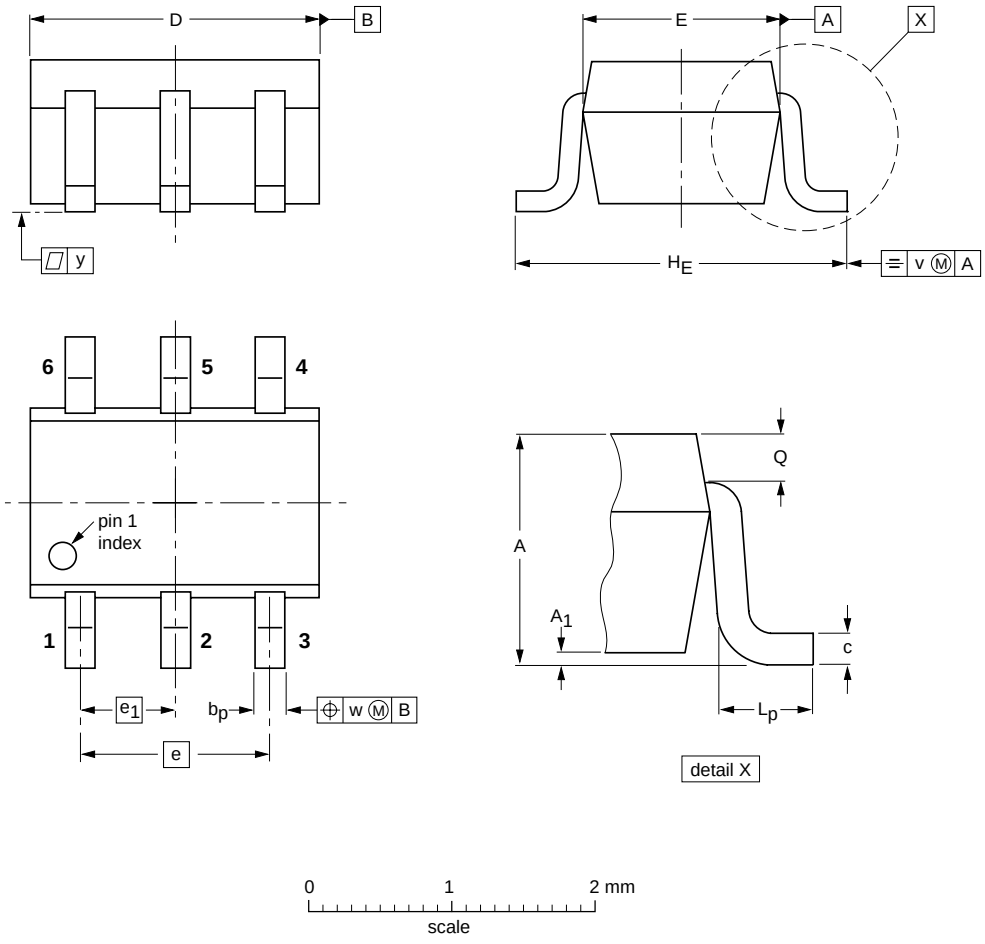
V_{gen} = generator voltage.

Fig 22. Test circuit for measuring charge injection

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12. Package outline

Plastic surface-mounted package; 6 leads **SOT363**



DIMENSIONS (mm are the original dimensions)

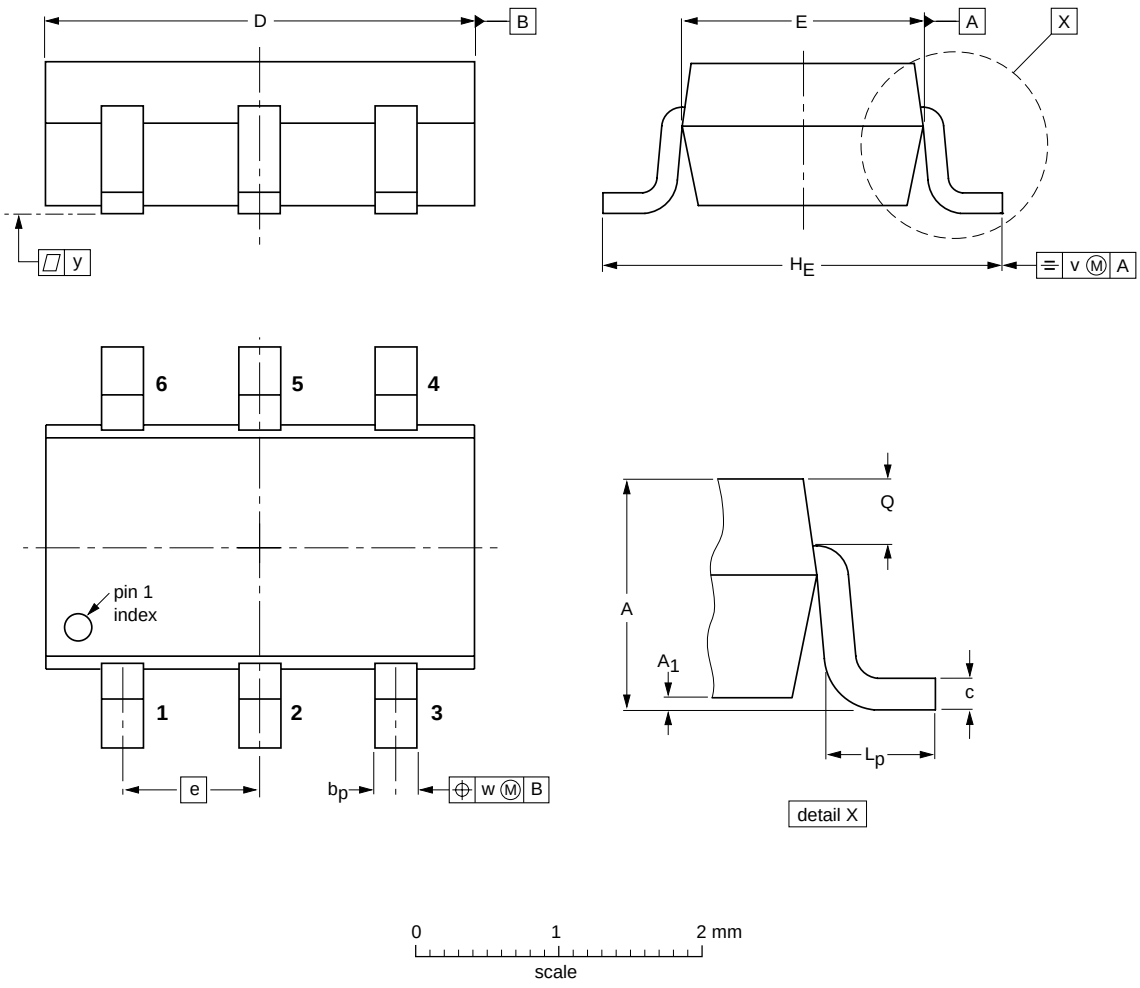
UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT363			SC-88			~~04-11-08~~ 06-03-16

Fig 23. Package outline SOT363 (SC-88)

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Plastic surface-mounted package (TSOP6); 6 leads **SOT457**



DIMENSIONS (mm are the original dimensions)

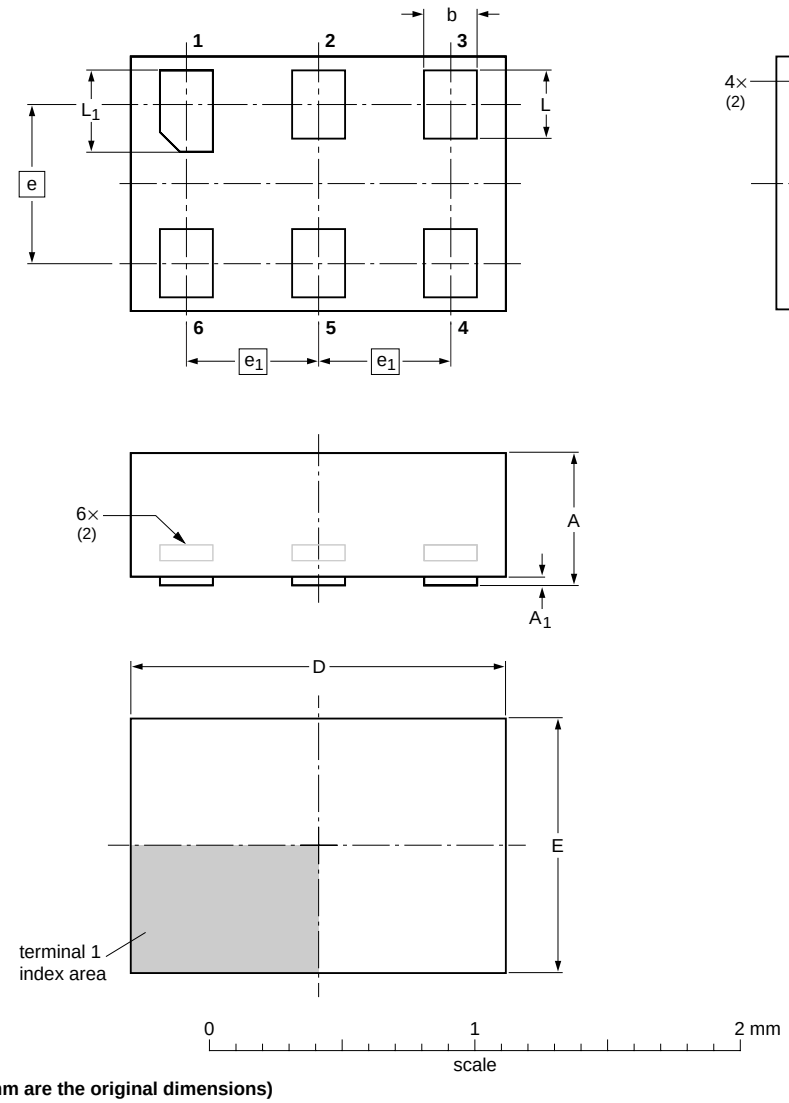
UNIT	A	A_1	b_p	c	D	E	e	H_E	L_p	Q	v	w	y
mm	1.1 0.9	0.1 0.013	0.40 0.25	0.26 0.10	3.1 2.7	1.7 1.3	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT457			SC-74			~~05-11-07~~ 06-03-16

Fig 24. Package outline SOT457 (SC-74)

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XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm **SOT886**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1) max	A1 max	b	D	E	e	e1	L	L1
mm	0.5	0.04	0.25 0.17	1.5 1.4	1.05 0.95	0.6	0.5	0.35 0.27	0.40 0.32

Notes

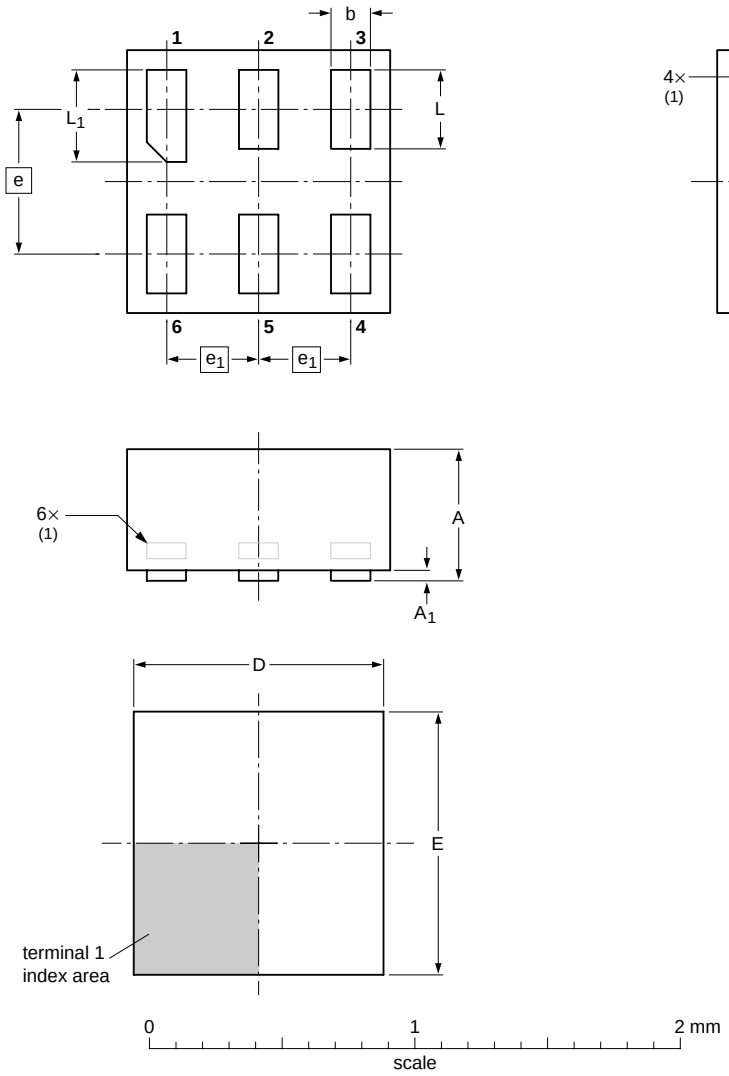
1. Including plating thickness.
2. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT886		MO-252				~~04-07-15~~ 04-07-22

Fig 25. Package outline SOT886 (XSON6)

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XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm **SOT891**



DIMENSIONS (mm are the original dimensions)

UNIT	A max	A_1 max	b	D	E	e	e_1	L	L_1
mm	0.5	0.04	0.20 0.12	1.05 0.95	1.05 0.95	0.55	0.35	0.35 0.27	0.40 0.32

Note

1. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT891						~~05-04-06~~ 07-05-15

Fig 26. Package outline SOT891 (XSON6)

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13. Abbreviations

Table 13. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
DUT	Device Under Test

14. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G3157_2	20070918	Product data sheet	-	74LVC1G3157_1
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name when appropriate. • Added type number 74LVC1G3157GF (XSON6 package). • Section 1 “General description”: Added: Schmitt trigger action at the enable input. • Section 2 “Features”: Added: Switch handling capability of 32 mA. • Section 8 “Limiting values”: Added: Derating factors of the applicable packages. • Section 10 “Static characteristics”: Changed: Maximum values of ON resistance (peak) parameters and graphics. Changed: Conditions for input leakage and supply current. Changed: Conditions for OFF-state and ON-state leakage current. • Section 11 “Dynamic characteristics”: Changed: Typical values of the charge injection.			
74LVC1G3157_1	20050207	Product data sheet	-	-

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15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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